The Memory Hierarchy

15-213/15-513: Introduction to Computer Systems 9th Lecture, June 8, 2023

Instructors:

Brian Railing

Today

- The memory abstraction
- RAM: main memory building block
- Locality of reference
- The memory hierarchy
- Storage technologies and trends

Writing & Reading Memory

■Write

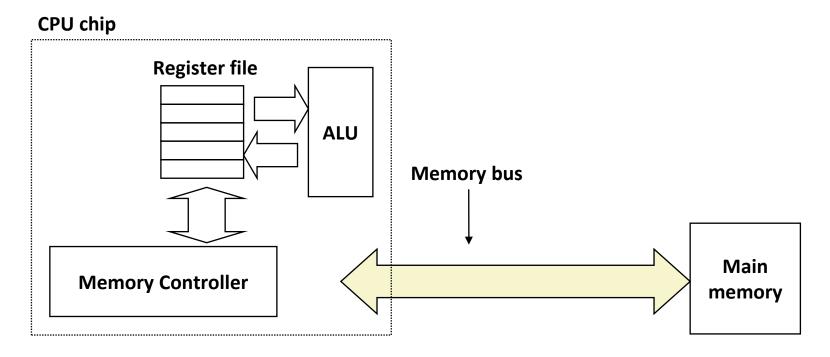
- Transfer data from CPU to memory movq %rax, 8(%rsp)
- "Store" operation

Read

- Transfer data from memory to CPU movq 8 (%rsp), %rax
- "Load" operation

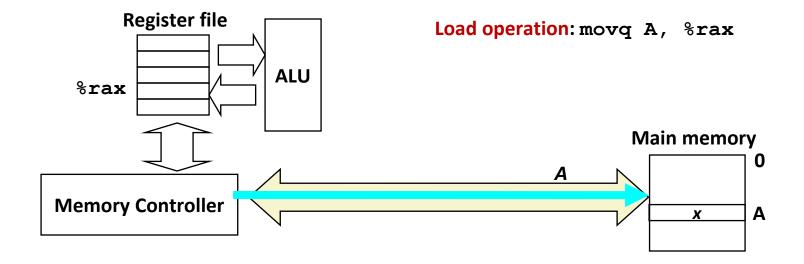
Modern Connection between CPU and Memory

- A bus is a collection of parallel wires that carry address, data, and control signals.
- Buses are typically shared by multiple devices.



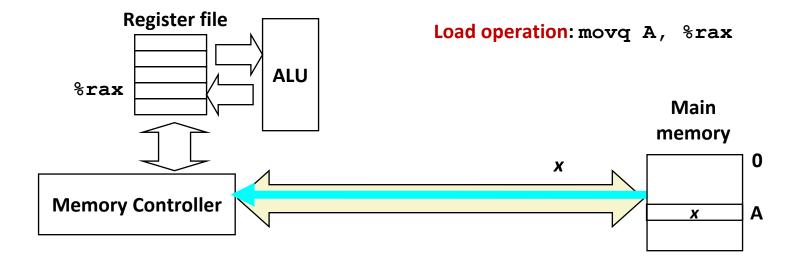
Memory Read Transaction (1)

CPU places address A on the memory bus.



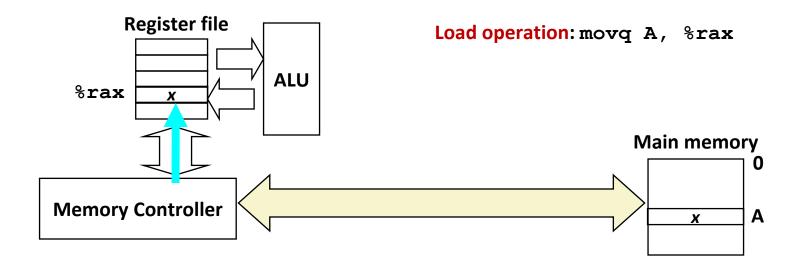
Memory Read Transaction (2)

■ Main memory reads A from the memory bus, retrieves word x, and places it on the bus.



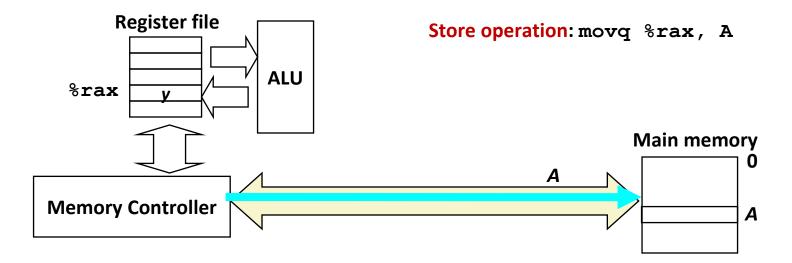
Memory Read Transaction (3)

■ CPU reads word x from the bus and copies it into register %rax.



Memory Write Transaction (1)

■ CPU places address A on bus. Main memory reads it and waits for the corresponding data word to arrive.



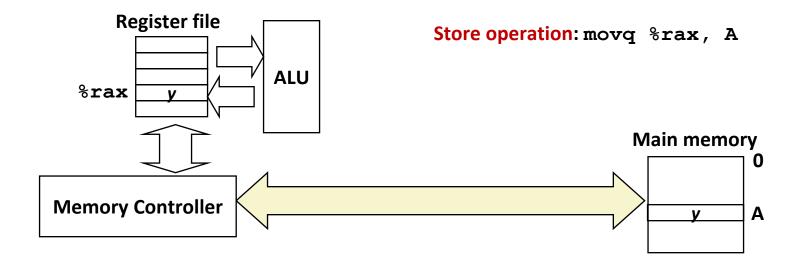
Memory Write Transaction (2)

CPU places data word y on the bus.



Memory Write Transaction (3)

Main memory reads data word y from the bus and stores it at address A.



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Random-Access Memory (RAM)

Key features

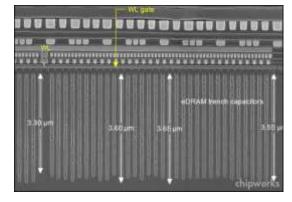
- RAM is traditionally packaged as a chip.
 - or embedded as part of processor chip
- Basic storage unit is normally a cell (one bit per cell).
- Multiple RAM chips form a memory.

RAM comes in two varieties:

- SRAM (Static RAM)
- DRAM (Dynamic RAM)

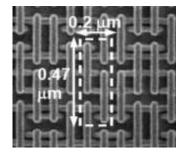
RAM Technologies

DRAM



- 1 Transistor + 1 capacitor / bit
 - Capacitor oriented vertically
- Must refresh state periodically

SRAM



- **■** 6 transistors / bit
- Holds state indefinitely

SRAM vs DRAM Summary

	Trans. per bit		Needs refresh		Cost	Applications
SRAM	6 or 8	1x	No	Maybe	100x	Cache memories
DRAM	1	10x	Yes	Yes	1x	Main memories, frame buffers

EDC: Error detection and correction

Trends

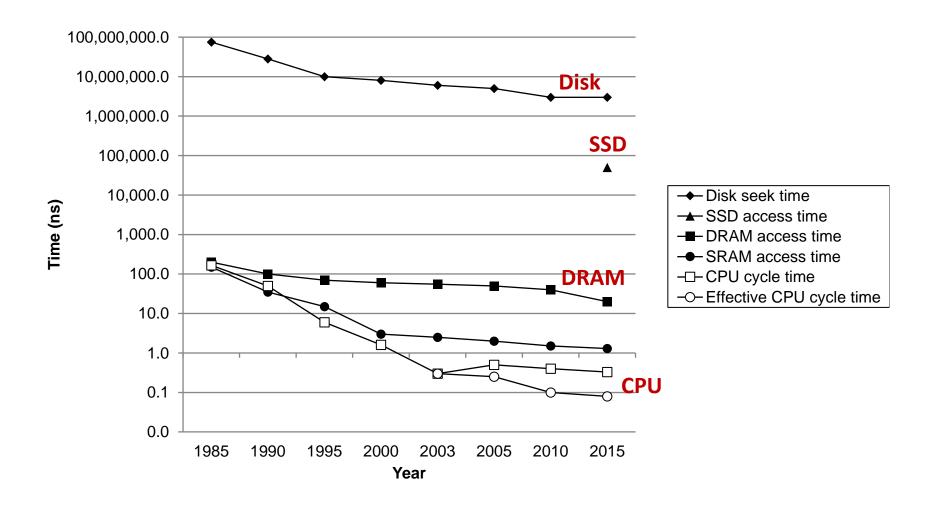
- SRAM scales with semiconductor technology
 - Reaching its limits
- DRAM scaling limited by need for minimum capacitance
 - Aspect ratio limits how deep can make capacitor
 - Also reaching its limits

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The CPU-Memory Gap

The gap widens between DRAM, disk, and CPU speeds.



Locality to the Rescue!

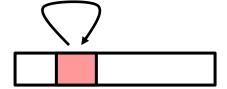
The key to bridging this CPU-Memory gap is an important property of computer programs known as locality.

Locality

Principle of Locality: Many Programs tend to use data and instructions with addresses near or equal to those they have used recently.

Temporal locality:

 Recently referenced items are likely to be referenced again in the near future



Spatial locality:

 Items with nearby addresses tend to be referenced close together in time



Locality Example

```
sum = 0;
for (i = 0; i < n; i++)
    sum += a[i];
return sum;</pre>
```

Data references

- Reference array elements in succession (stride-1 reference pattern).
- Reference variable sum each iteration.

Instruction references

- Reference instructions in sequence.
- Cycle through loop repeatedly.

Spatial or Temporal Locality?

spatial

temporal

spatial temporal

Qualitative Estimates of Locality

■ Claim: Being able to look at code and get a qualitative sense of its locality is a key skill for a professional programmer.

Question: Does this function have good locality with

respect to array a?

Hint: array layout is row-major order

Answer: yes

```
int sum_array_rows(int a[M][N])
{
    int i, j, sum = 0;

    for (i = 0; i < M; i++)
        for (j = 0; j < N; j++)
            sum += a[i][j];
    return sum;
}</pre>
```

a		a	a		a		a		a
[0]	• • •	[0]	[1]	• • •	[1]	• • •	[M-1]	• • •	[M-1]
[0]		[N-1]	[0]		[N-1]		[0]		[N-1]

Locality Example

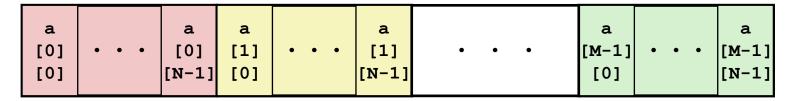
Question: Does this function have good locality with respect to array a?

```
int sum_array_cols(int a[M][N])
{
   int i, j, sum = 0;

   for (j = 0; j < N; j++)
        for (i = 0; i < M; i++)
            sum += a[i][j];
   return sum;
}</pre>
```

Answer: no, unless...

M is very small



Locality Example

Question: Can you permute the loops so that the function scans the 3-d array a with a stride-1 reference pattern (and thus has good spatial locality)?

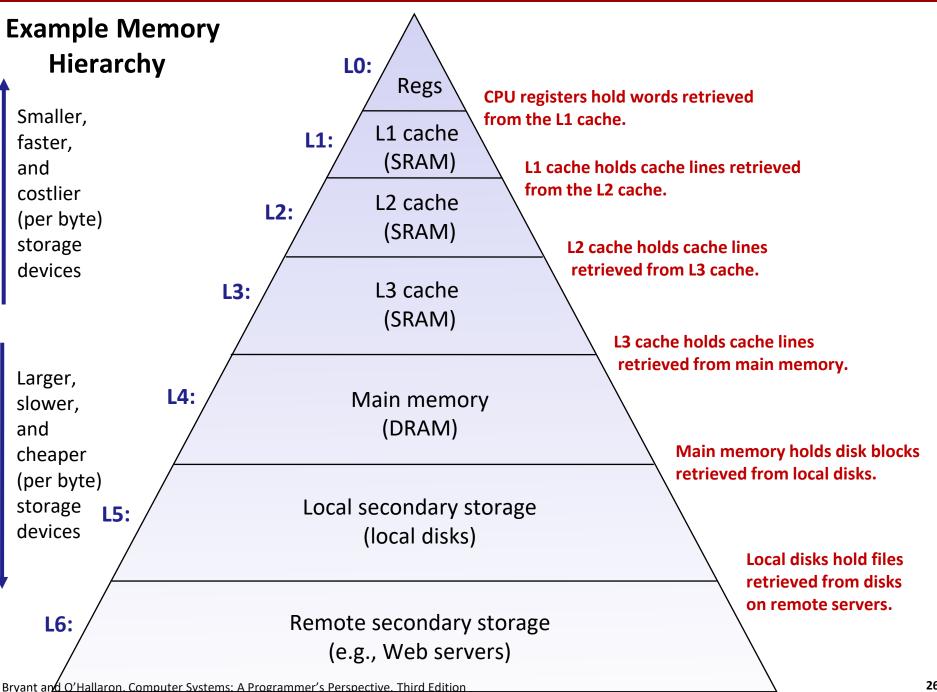
Answer: make j the inner loop

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Memory Hierarchies

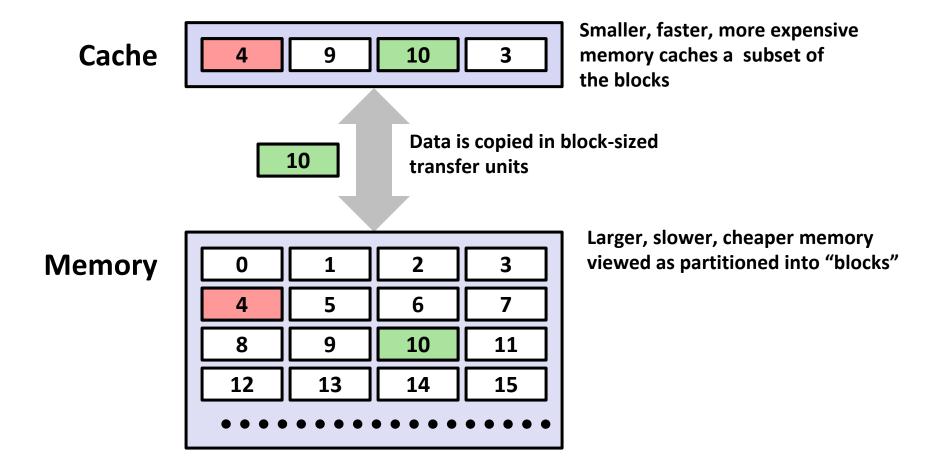
- Some fundamental and enduring properties of hardware and software:
 - Fast storage technologies cost more per byte, have less capacity, and require more power (heat!).
 - The gap between CPU and main memory speed is widening.
 - Well-written programs tend to exhibit good locality.
- These properties complement each other well for many types of programs.
- They suggest an approach for organizing memory and storage systems known as a memory hierarchy.



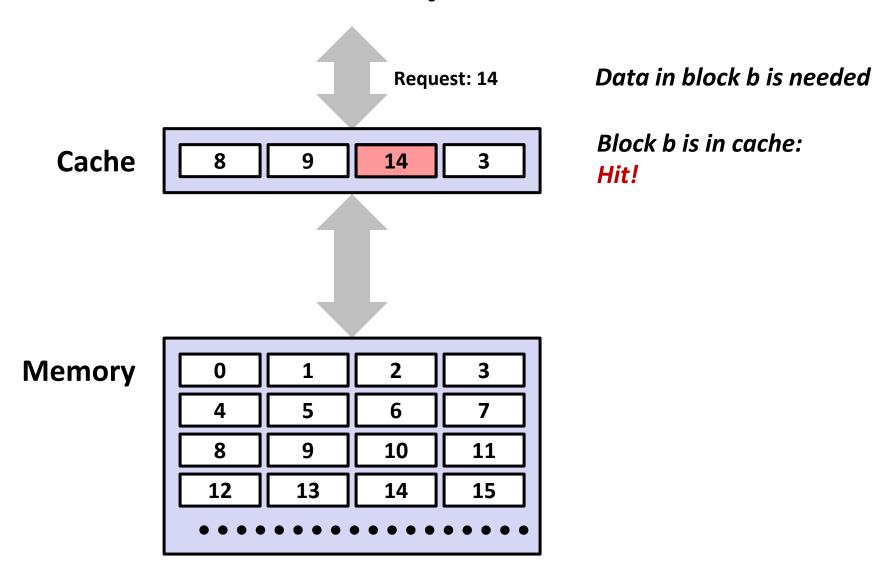
Caches

- Cache: A smaller, faster storage device that acts as a staging area for a subset of the data in a larger, slower device.
- Fundamental idea of a memory hierarchy:
 - For each k, the faster, smaller device at level k serves as a cache for the larger,
 slower device at level k+1.
- Why do memory hierarchies work?
 - Because of locality: programs tend to access the data at level k more often than they access the data at level k+1.
 - Thus, the storage at level k+1 can be slower, and thus larger and cheaper per bit.
- Big Idea (Ideal): The memory hierarchy creates a large pool of storage that costs as much as the cheap storage near the bottom, but that serves data to programs at the rate of the fast storage near the top.

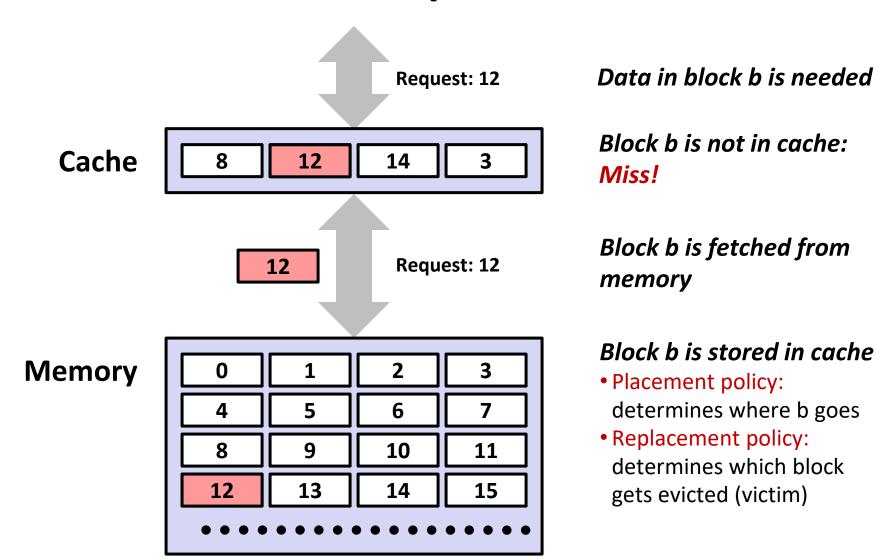
General Cache Concepts



General Cache Concepts: Hit



General Cache Concepts: Miss



General Caching Concepts: 3 Types of Cache Misses

■ Cold (compulsory) miss

 Cold misses occur because the cache starts empty and this is the first reference to the block.

Capacity miss

 Occurs when the set of active cache blocks (working set) is larger than the cache.

Conflict miss

- Most caches limit blocks at level k+1 to a small subset (sometimes a singleton) of the block positions at level k.
 - E.g. Block i at level k+1 must be placed in block (i mod 4) at level k.
- Conflict misses occur when the level k cache is large enough, but multiple data objects all map to the same level k block.
 - E.g. Referencing blocks 0, 8, 0, 8, 0, 8, ... would miss every time.

Examples of Caching in the Mem. Hierarchy

Cache Type	What is Cached?	Where is it Cached?	Latency (cycles)	Managed By
Registers	4-8 byte words	CPU core	0	Compiler
TLB	Address translations	On-Chip TLB	0	Hardware MMU
L1 cache	64-byte blocks	On-Chip L1	4	Hardware
L2 cache	64-byte blocks	On-Chip L2	10	Hardware
Virtual Memory	4-KB pages	Main memory	100	Hardware + OS
Buffer cache	Parts of files	Main memory	100	os
Disk cache	Disk sectors	Disk controller	100,000	Disk firmware
Network buffer cache	Parts of files	Local disk	10,000,000	NFS client
Browser cache	Web pages	Local disk	10,000,000	Web browser
Web cache	Web pages	Remote server disks	1,000,000,000	Web proxy server

Quiz

https://canvas.cmu.edu/courses/34989/quizzes/103051

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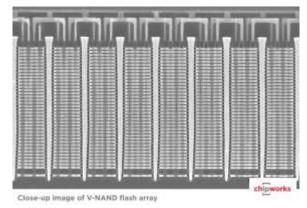
Storage Technologies

Magnetic Disks



- Store on magnetic medium
- Electromechanical access

Nonvolatile (Flash)
Memory



- Store as persistent charge
- Implemented with 3-D structure
 - 100+ levels of cells
 - 3-4 bits data per cell

What's Inside A Disk Drive?

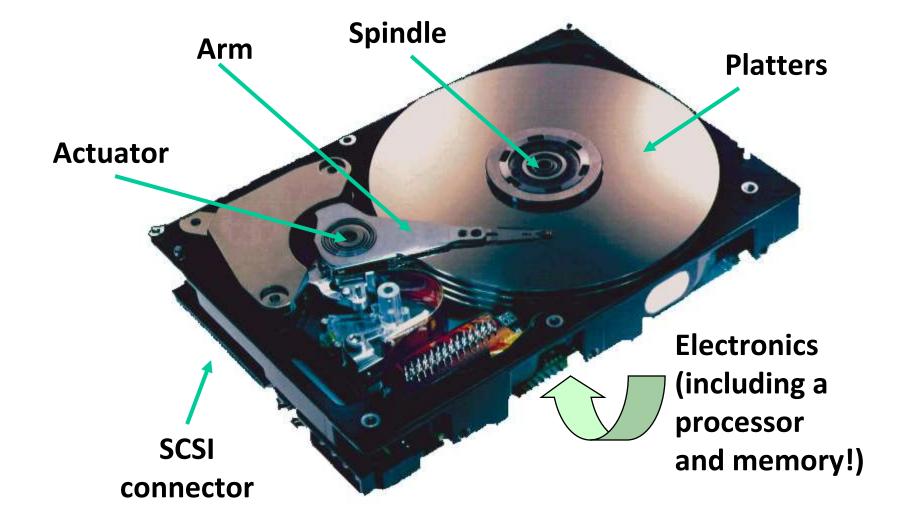
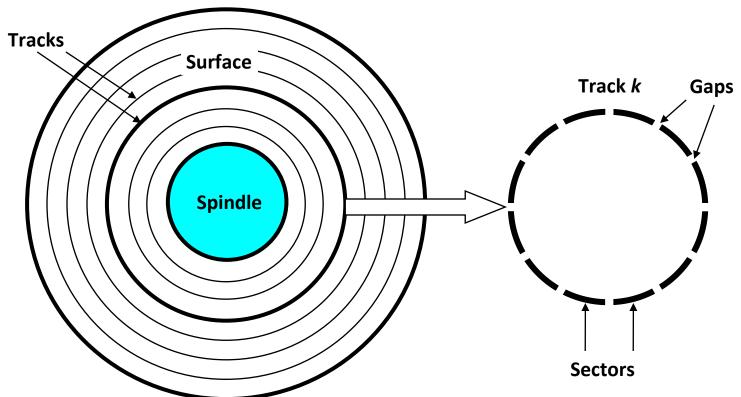


Image courtesy of Seagate Technology

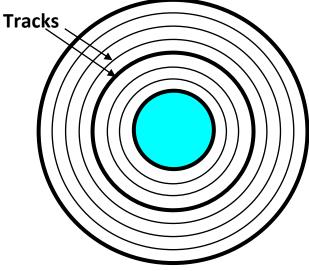
Disk Geometry

- Disks consist of platters, each with two surfaces.
- Each surface consists of concentric rings called tracks.
- Each track consists of sectors separated by gaps.

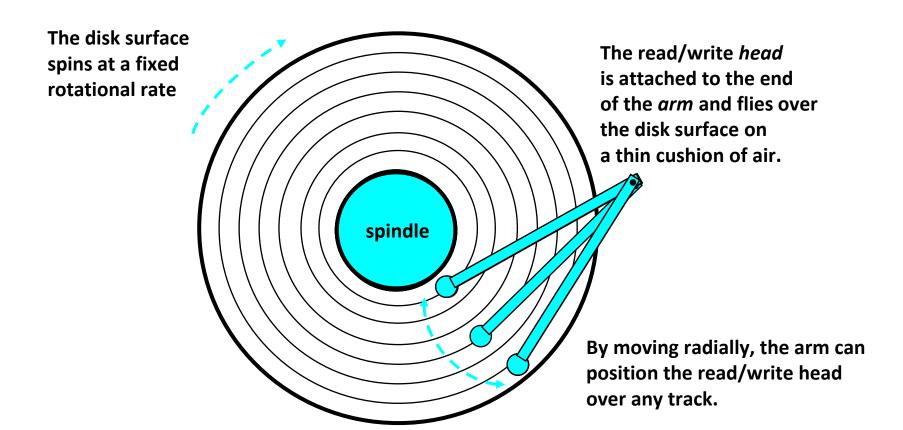


Disk Capacity

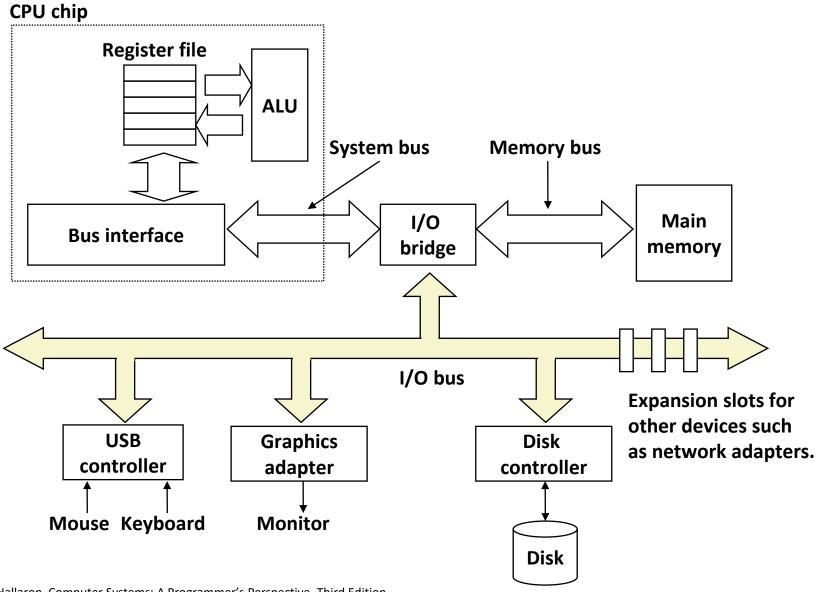
- Capacity: maximum number of bits that can be stored.
 - Vendors express capacity in units of gigabytes (GB) or terabytes (TB),
 where 1 GB = 10⁹ Bytes and 1 TB = 10¹² Bytes
- Capacity is determined by these technology factors:
 - Recording density (bits/in): number of bits that can be squeezed into a 1 inch segment of a track.
 - Track density (tracks/in): number of tracks that can be squeezed into a 1 inch radial segment.
 - Areal density (bits/in²): product of recording and track density.



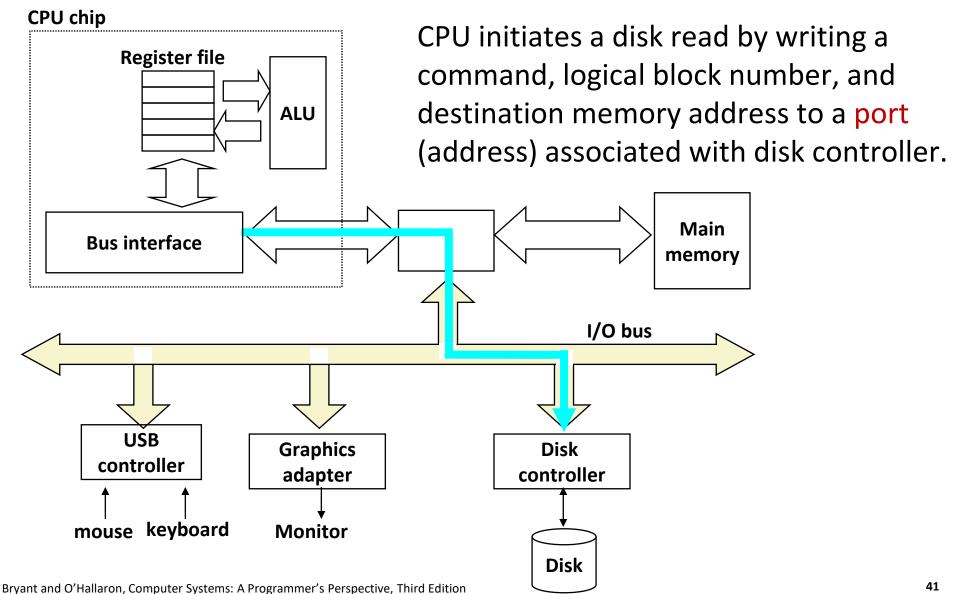
Disk Operation (Single-Platter View)



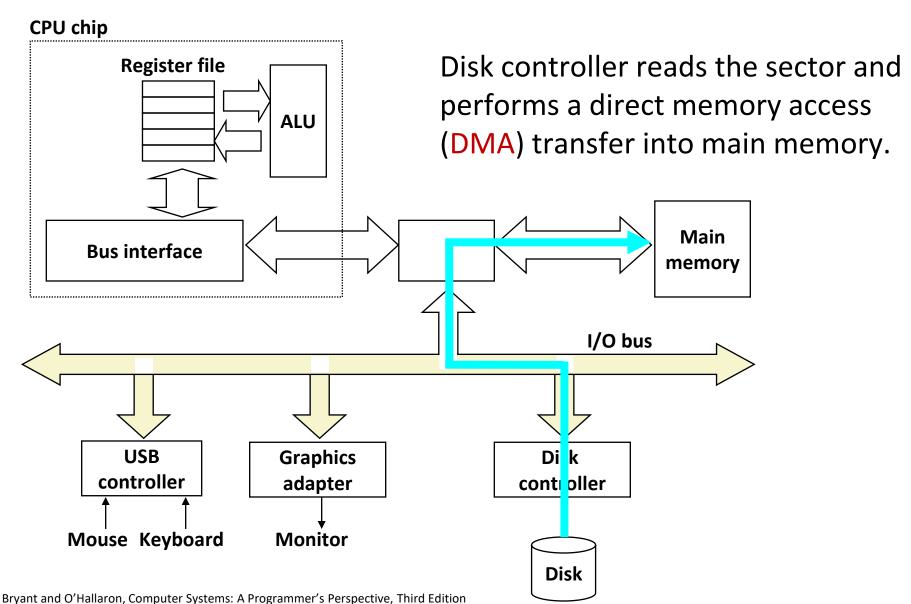
I/O Bus



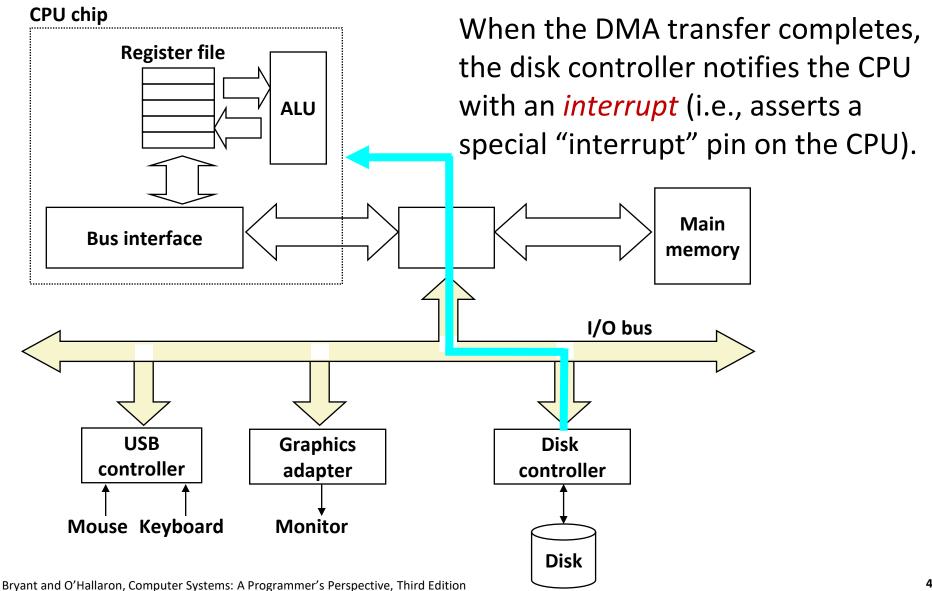
Reading a Disk Sector (1)



Reading a Disk Sector (2)



Reading a Disk Sector (3)



Nonvolatile Memories

■ DRAM and SRAM are volatile memories

Lose information if powered off.

■ Nonvolatile memories retain value even if powered off

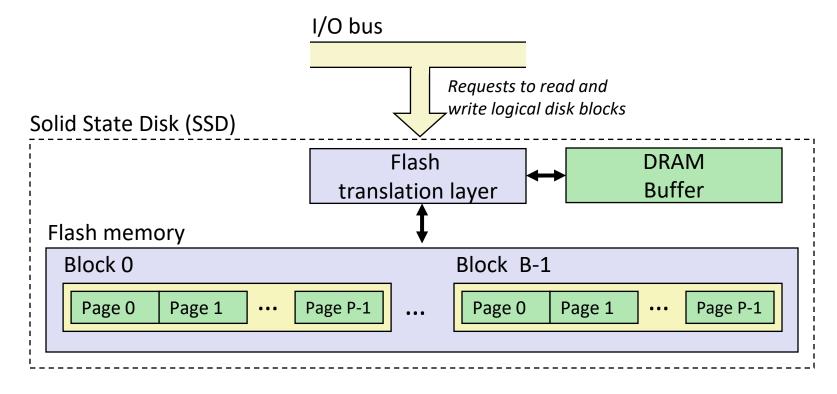
- Read-only memory (ROM): programmed during production
- Electrically eraseable PROM (EEPROM): electronic erase capability
- Flash memory: EEPROMs, with partial (block-level) erase capability
 - Wears out after about 100,000 erasings
- 3D XPoint (Intel Optane) & emerging NVMs
 - New materials



Uses for Nonvolatile Memories

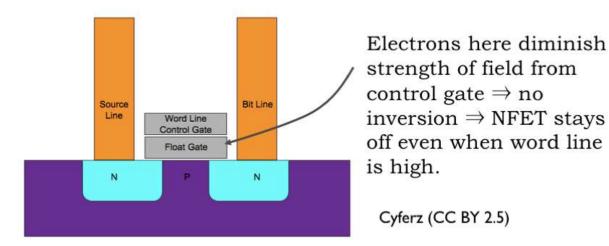
- Firmware programs stored in a ROM (BIOS, controllers for disks, network cards, graphics accelerators, security subsystems,...)
- Solid state disks (replacing rotating disks)
- Disk caches

Solid State Disks (SSDs)



- Pages: 512KB to 4KB, Blocks: 32 to 128 pages
- Data read/written in units of pages.
- Page can be written only after its block has been erased.
- A block wears out after about 10,000 repeated writes.

Non-Volatile Storage: Flash



Flash Memory: Use "floating gate" transistors to store charge

- Very dense: Multiple bits/transistor, read and written in blocks
- Slow (especially on writes), 10-100 us
- Limited number of writes: charging/discharging the floating gate (writes) requires large voltages that damage transistor

SSD Performance Characteristics

Benchmark of Samsung 970 EVO Plus

https://ssd.userbenchmark.com/SpeedTest/711305/Samsung-SSD-970-EVO-Plus-250GB

Sequential read throughput 2,221 MB/s Sequential write tput 1,912 MB/s
Random ST throughput 61.7 MB/s Random write tput 165 MB/s
Random DQ throughput 947 MB/s Random DQ write 1028 MB/s

Sequential access faster than random access

- Common theme in the memory hierarchy
- DQ = deep queue, issuing many concurrent reads (latency hurts!)

Random writes are tricky

- Erasing a block takes a long time (~1 ms), but the SSD has a pool of preerased blocks
- Modifying a block page requires all other pages to be copied to new block.
- But the SSD has a write cache that it accumulates writes into...

SSD Tradeoffs vs Rotating Disks

Advantages

No moving parts → faster, less power, more rugged

Disadvantages

- Have the potential to wear out
 - Mitigated by "wear leveling logic" in flash translation layer
 - E.g. Samsung 940 EVO Plus guarantees 600 writes/byte of writes before they wear out
 - Controller migrates data to minimize wear level
- In 2022, about 4-5 times more expensive per byte
 - And, relative cost will keep dropping

Where are are rotating disks still used?

- Bulk storage video, huge datasets / databases, etc.
- Cheap storage desktops.

Summary

- The speed gap between CPU, memory and mass storage continues to widen.
- **■** Well-written programs exhibit a property called *locality*.
- Memory hierarchies based on caching close the gap by exploiting locality.
- Flash memory progress outpacing all other memory and storage technologies (DRAM, SRAM, magnetic disk)
 - Able to stack cells in three dimensions

Supplemental slides

Storage Trends

SRAM

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/MB	2,900	320	256	100	75	60	320	116
access (ns)	150	35	15	3	2	1.5	200	115

DRAM

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/MB	880	100	30	1	0.1	0.06	0.02	44,000
access (ns) typical size (MB)	200 0.256	100 4	70 16	60 64	50 2,000	40 8,000	20 16.000	10 62,500

Disk

Metric	1985	1990	1995	2000	2005	2010	2015	2015:1985
\$/GB	100,000	8,000	300	10	5	0.3	0.03	3,333,333
access (ms)	75	28	10	8	5	3	3	25
typical size (GB)	0.01	0.16	1	20	160	1,500	3,000	300,000

CPU Clock Rates

Inflection point in computer history when designers hit the "Power Wall"

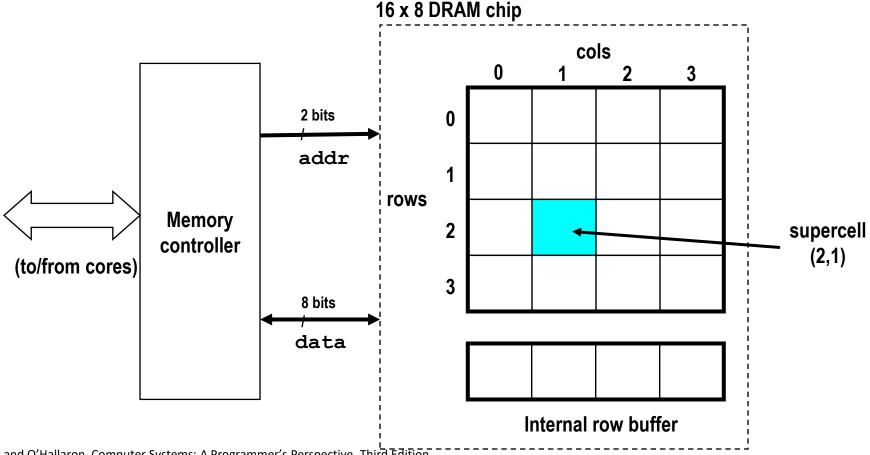
			1				
1985	1990	1995	2003	2005	2010	2015	2015:1985
80286	80386	Pentium	P-4	Core 2	Core i7(n) Core i7(h	
) 6	20	150	3,300	2,000	2,500	3,000	500
166	50	6	0.30	0.50	0.4	0.33	500
1	1	1	1	2	4	4	4
166	50	6	0.30	0.25	0.10	0.08	2,075
	80286) 6 166 1	80286 80386) 6 20 166 50 1 1	80286 80386 Pentium) 6 20 150 166 50 6 1 1 1	80286 80386 Pentium P-4) 6 20 150 3,300 166 50 6 0.30 1 1 1 1	80286 80386 Pentium P-4 Core 2) 6 20 150 3,300 2,000 166 50 6 0.30 0.50 1 1 1 2	80286 80386 Pentium P-4 Core 2 Core i7(n 0 6 20 150 3,300 2,000 2,500 166 50 6 0.30 0.50 0.4 1 1 1 2 4	80286 80386 Pentium P-4 Core 2 Core i7(n) Core i7(h) 1 6 20 150 3,300 2,000 2,500 3,000 166 50 6 0.30 0.50 0.4 0.33 1 1 1 1 1 2 4 4

(n) Nehalem processor(h) Haswell processor

Conventional DRAM Organization

dxw DRAM:

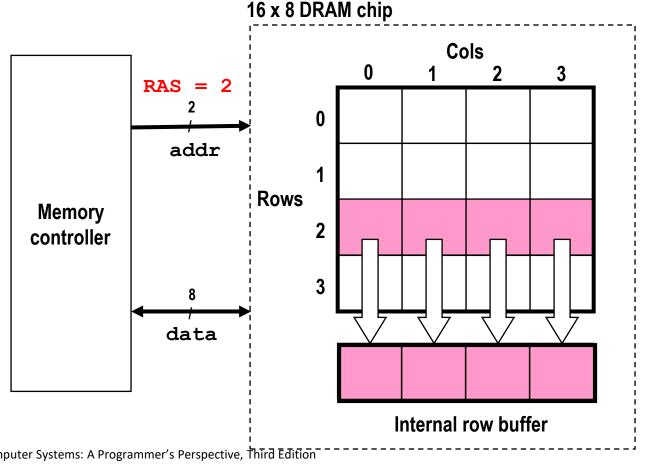
 $d \cdot w$ total bits organized as d supercells of size w bits



Reading DRAM Supercell (2,1)

Step 1(a): Row access strobe (RAS) selects row 2.

Step 1(b): Row 2 copied from DRAM array to row buffer.

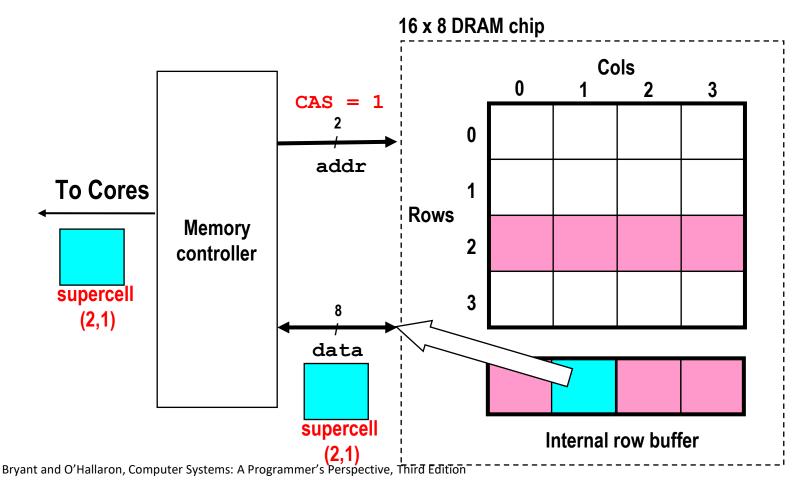


Reading DRAM Supercell (2,1)

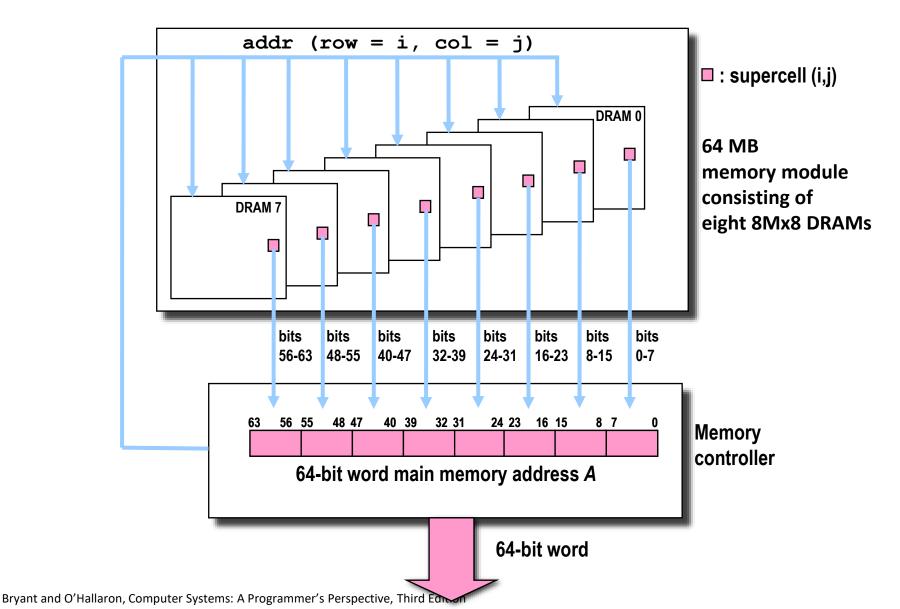
Step 2(a): Column access strobe (CAS) selects column 1.

Step 2(b): Supercell (2,1) copied from buffer to data lines, and eventually back to the CPU.

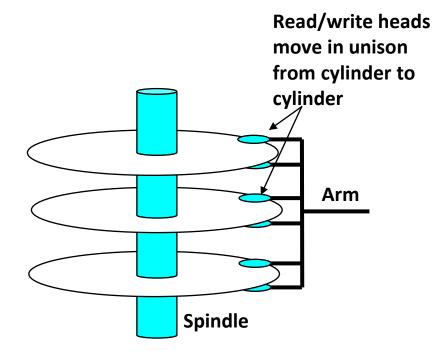
Step 3: All data written back to row to provide refresh



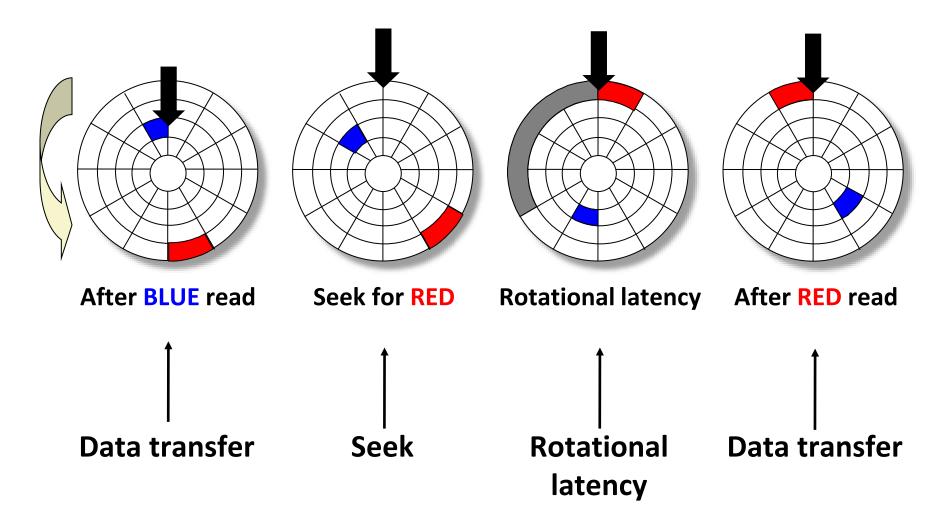
Memory Modules



Disk Operation (Multi-Platter View)



Disk Access – Service Time Components



Disk Access Time

Average time to access some target sector approximated by:

 $T_{access} = T_{avg seek} + T_{avg rotation} + T_{avg transfer}$

Seek time (T_{avg seek})

- Time to position heads over cylinder containing target sector.
- Typical T_{avg seek} is 3—9 ms

Rotational latency (T_{avg rotation})

- Time waiting for first bit of target sector to pass under r/w head.
- $T_{avg\ rotation} = 1/2 \times 1/RPMs \times 60 \sec/1 \min$
- Typical rotational rate = 7,200 RPMs

■ Transfer time (T_{avg transfer})

- Time to read the bits in the target sector.
- T_{avg transfer} = 1/RPM x 1/(avg # sectors/track) x 60 secs/1 min

time for one rotation (in minutes) fraction of a rotation to be read

Disk Access Time Example

Given:

- Rotational rate = 7,200 RPM
- Average seek time = 9 ms
- Avg # sectors/track = 400

Derived:

- T_{avg rotation} = 1/2 x (60 secs/7200 RPM) x 1000 ms/sec = 4 ms
- $T_{avg\ transfer} = 60/7200\ x\ 1/400\ x\ 1000\ ms/sec = 0.02\ ms$
- $T_{access} = 9 \text{ ms} + 4 \text{ ms} + 0.02 \text{ ms}$

Important points:

- Access time dominated by seek time and rotational latency.
- First bit in a sector is the most expensive, the rest are free.
- SRAM access time is about 4 ns/doubleword, DRAM about 60 ns
 - Disk is about 40,000 times slower than SRAM,
 - 2,500 times slower than DRAM.